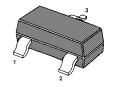
## SURFACE MOUNT SWITCHING DIODE

#### **Features**

- · Fast switching speed
- High Conductance





Marking Code: **5D** SOT-23 Plastic Package

### **Applications**

• For general purpose switching

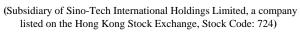
### Absolute Maximum Ratings (T<sub>a</sub> = 25 °C)

Parameter		Symbol	Value	Unit
Peak Reverse Voltage		$V_{RM}$	100	V
Reverse Voltage		$V_R$	75	V
Average Rectified Output Current		Io	250	mA
Forward Continuous Current		I <sub>FM</sub>	500	mA
Non-repetitive Peak Forward Surge Current	at t = 1 µs at t = 1 s	I <sub>FSM</sub>	4 2	Α
Power Dissipation		P <sub>d</sub>	350	mW
Junction and Storage Temperature Range		T <sub>j</sub> , T <sub>S</sub>	- 65 to + 150	°C

# Characteristics at $T_a = 25$ °C

Parameter	Symbol	Min.	Max.	Unit
Forward Voltage at $I_F = 5$ mA at $I_F = 10$ mA at $I_F = 100$ mA at $I_F = 150$ mA	V <sub>F</sub>	0.62 - - -	0.72 0.855 1 1.25	>
Reverse Current at $V_R$ = 20 V at $V_R$ = 75 V at $V_R$ = 25 V, $T_j$ = 150 °C at $V_R$ = 75 V, $T_j$ = 150 °C	I <sub>R</sub>	- - -	25 2.5 30 50	nΑ μΑ μΑ μΑ
Junction Capacitance at $V_R = 0 \text{ V}$ , $f = 1 \text{ MHz}$	C <sub>j</sub>	-	4	pF
Reverse Recovery Time at $I_F = I_R = 10$ mA, $I_{rr} = 0.1$ X $I_R$ , $R_L = 100$ $\Omega$	t <sub>rr</sub>	-	4	ns



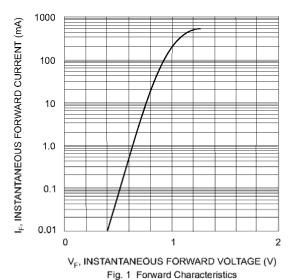


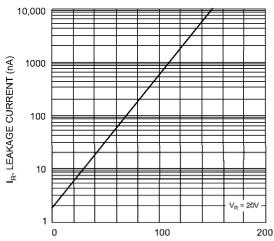






Dated: 10/10/2008





 $T_j$ , JUNCTION TEMPERATURE (°C) Fig. 2 Leakage Current vs Junction Temperature



# SEMTECH ELECTRONICS LTD.

(Subsidiary of Sino-Tech International Holdings Limited, a company listed on the Hong Kong Stock Exchange, Stock Code: 724)







Dated: 10/10/2008